

Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (currently amended) A method for processing one or more semiconductor wafers, the method comprising the steps of:
providing one or more semiconductor wafers in a processing chamber; ~~and~~
rinsing the one or more semiconductor wafers in the processing chamber;
introducing a gaseous antistatic agent comprising carbon dioxide gas into
the processing chamber during at least a portion of the rinsing step;
drying the one or more semiconductor wafers in the processing chamber;
and
introducing a gaseous antistatic agent comprising carbon dioxide gas into
the processing chamber wherein during at least a portion of the
drying step, the one or more semiconductor wafers are in the
presence of an antistatic agent.
2. (original) The method of claim 1, wherein the step of drying the one or more semiconductor wafers comprises flowing a drying gas into the processing chamber.
3. (original) The method of claim 2, wherein the drying gas comprises gaseous nitrogen.
4. (cancelled)
5. (cancelled)
6. (original) The method of claim 1, wherein the step of drying the one or more semiconductor wafers comprises introducing a drying enhancement substance into the processing chamber.

7. (original) The method of claim 6, wherein the drying enhancement substance comprises isopropyl alcohol.
8. (cancelled)
9. (currently amended) The method of ~~claim 8~~, claim 1, wherein the ~~at least one additional processing step comprises a rinsing step that precedes the drying step.~~
- 10-25. (cancelled)
26. (new) A method for processing one or more semiconductor wafers, the method comprising the steps of:
 - providing one or more semiconductor wafers in a processing chamber;
 - rinsing the one or more semiconductor wafers in the processing chamber;
 - introducing a gaseous antistatic agent into the processing chamber during
 - at least a portion of the rinsing step;
 - drying the one or more semiconductor wafers in the processing chamber;
 - and
 - introducing a gaseous antistatic agent into the processing chamber during
 - at least a portion of the drying step;
 - wherein the gaseous antistatic agent introduced during the rinsing step and the gaseous antistatic agent introduced during the drying step independently comprise a gaseous antistatic agent selected from ionized clean dry air and carbon dioxide.
27. (new) The method of claim 26, wherein the step of drying the one or more semiconductor wafers comprises flowing a drying gas into the processing chamber.
28. (new) The method of claim 27, wherein the drying gas comprises gaseous nitrogen.

29. (new) The method of claim 26, wherein the gaseous antistatic agent present during at least a portion of the rinsing step comprises ionized clean dry air and the gaseous antistatic agent introduced during at least a portion of the rinsing step comprises ionized clean dry air.
30. (new) The method of claim 26, wherein the step of drying the one or more semiconductor wafers comprises introducing a drying enhancement substance into the processing chamber.
31. (new) The method of claim 30, wherein the drying enhancement substance comprises isopropyl alcohol.
32. (new) The method of claim 26, wherein the rinsing step precedes the drying step.
33. (new) A method for processing one or more semiconductor wafers, the method comprising the steps of:
 - providing one or more semiconductor wafers in a processing chamber;
 - rinsing the one or more semiconductor wafers in the processing chamber;
 - introducing a gaseous antistatic agent into the processing chamber during
at least a portion of the rinsing step;
 - drying the one or more semiconductor wafers in the processing chamber;
 - introducing a gaseous antistatic agent into the processing chamber during
at least a portion of the drying step; and
 - introducing a drying enhancement substance into the processing chamber
during at least a portion of the drying step.
34. (new) The method of claim 33, wherein at least one of the gaseous antistatic agent introduced during the rinsing step and the gaseous antistatic agent introduced during the drying step comprises carbon dioxide.

35. (new) The method of claim 33, wherein at least one of the gaseous antistatic agent introduced during the rinsing step and the gaseous antistatic agent introduced during the drying step comprises ionized clean dry air.
36. (new) The method of claim 33, wherein the drying enhancement substance comprises isopropyl alcohol.